

# MJD47

# HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

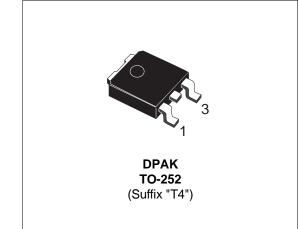
- STMicroelectronics PREFERRED SALESTYPE
- HIGH VOLTAGE CAPABILITY
- SURFACE-MOUNTING TO-252 (DPAK) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")
- ELECTRICALLY SIMILAR TO TIP47

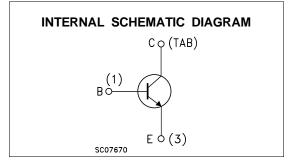
#### **APPLICATIONS**

- SWITCH MODE POWER SUPPLIES
- AUDIO AMPLIFIERS
- GENERAL PURPOSE SWITCHING AND AMPLIFIER

#### DESCRIPTION

The MJD47 is manufactured using Medium Voltage Epitaxial Planar technology, resulting in a rugged high performance cost-effective transistor.





#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>СВО</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)	350	V
Vceo	Collector-Emitter Voltage (I <sub>B</sub> = 0)	250	V
V <sub>EBO</sub>	Emitter-Base Voltage $(I_{C} = 0)$	5	V
Ιc	Collector Current	1	A
I <sub>CM</sub>	Collector Peak Current (t <sub>p</sub> < 5 ms)	2	A
IB	Base Current	0.6	A
I <sub>BM</sub>	Base Peak Current (t <sub>p</sub> < 5 ms)	1.2	A
Ptot	Total Dissipation at $T_c = 25 \ ^{\circ}C$	15	W
T <sub>stg</sub>	Storage Temperature	-65 to 150	
Tj	Max. Operating Junction Temperature	150	°C

#### January 2000

## THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	8.33	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Мах	100	°C/W

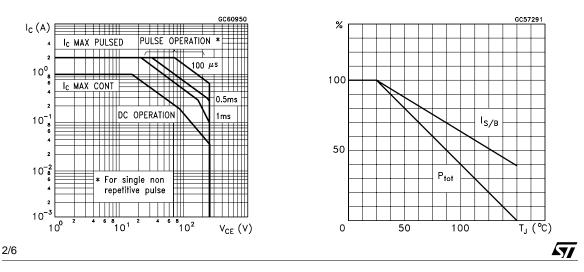
## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
ICES	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 350 V			0.1	mA
ICEO	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 150 V			0.1	mA
I <sub>EBO</sub>	Emitter Cut-off Current $(I_C = 0)$	$V_{EB} = 5 V$			1	mA
V <sub>CEO(sus)</sub> *	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	Ic = 30 mA	250			V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	$I_{\rm C} = 1 \ {\rm A}$ $I_{\rm B} = 0.2 \ {\rm A}$			1	V
$V_{BE(on)}*$	Base-Emitter On Voltage	I <sub>C</sub> = 1 A V <sub>CE</sub> = 10 V			1.5	V
h <sub>FE</sub> *	DC Current Gain		30 10		150	
f⊤	Transition Frequency	$I_{C} = 0.2 \text{ A}$ $V_{CE} = 10 \text{ V}$ f = 2MHz	10			MHz
h <sub>fe</sub>	Small Signal Current Gain	$I_{C} = 0.2 \text{ A}$ $V_{CE} = 10 \text{ V}$ f = 1KHz	25			

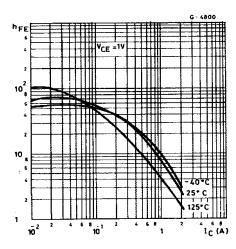
 $\ast$  Pulsed: Pulse duration = 300  $\mu s,$  duty cycle 1.5 %

### Safe Operating Area

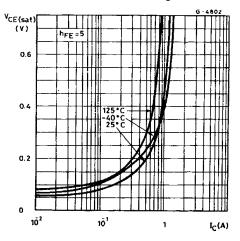
### **Derating Curves**



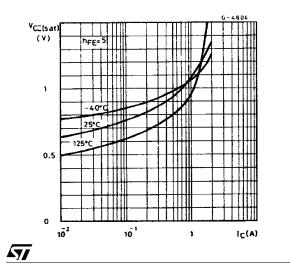
## DC Current Gain



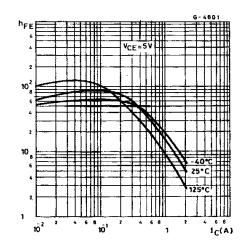
Collector-Emitter Saturation Voltage



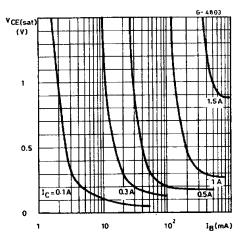
Base-Emitter Saturation Voltage



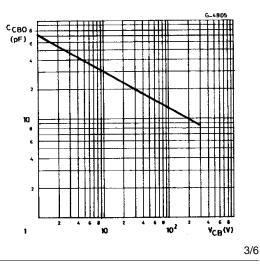
DC Current Gain



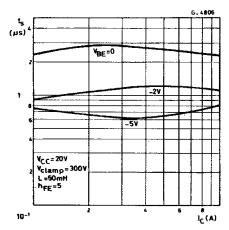
Collector-Emitter Saturation Voltage



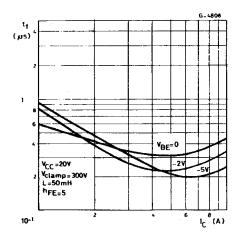
Collector-Base Capacitance



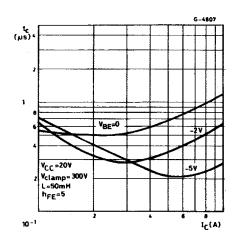
Switching Time Inductive Load



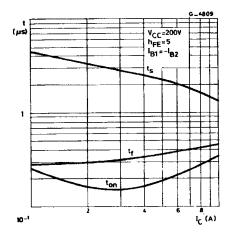
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Switching Time Inductive Load



Switching Time Inductive Load

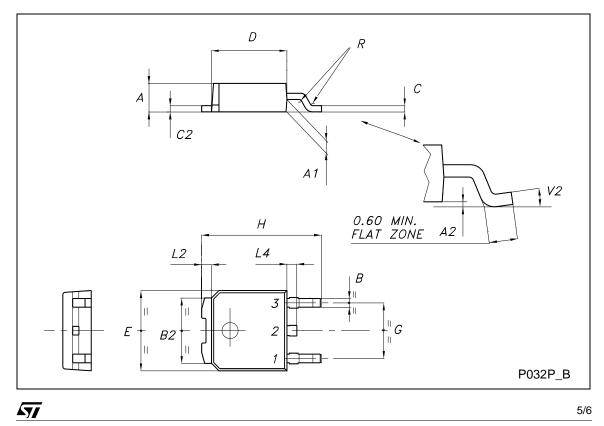


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DIM.	mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
С	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
Н	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0 <sup>0</sup>





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